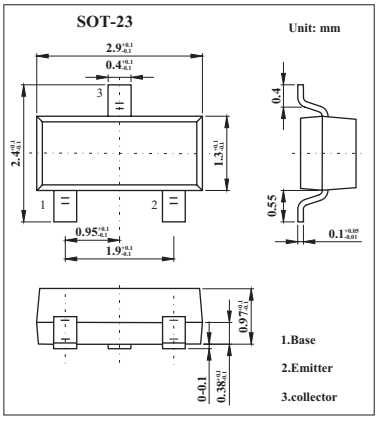
PNP General Purpose Amplifier

BSS63



Features

- PNP general purpose amplifier

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CE0}	100	V
Collector-base voltage	V_{CBO}	110	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	200	mA
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃
Total device dissipation Derate above 25℃	P_D	350 2.8	mW mW/℃
Thermal resistance, junction to ambient	$R_{\theta JA}$	357	℃/W

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 100 μA, I_B = 0	100			V
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10 μA, I_E = 0	110			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 1.0 μA, I_C = 0	6			V
Collector-cutoff current	I_{CBO}	V_{CB} = 90 V, I_E = 0			100	nA
		V_{CB} = 90 V, I_E = 0, T_A = 150℃			50	μA
Emitter-base cut-off current	I_{EBO}	V_{EB} = 6.0 V, I_C = 0			200	nA
DC current gain	h_{FE}	I_C = 10 mA, V_{CE} = 1.0 V	30			
		I_C = 25 mA, V_{CE} = 1.0 V	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 25 mA, I_B = 2.5 mA			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 25 mA, I_B = 2.5 mA			0.9	V
Current gain - bandwidth product	f_T	I_C = 25 mA, V_{CE} = 5.0,f = 35 MHz	50			MHz

Marking

Marking	T3